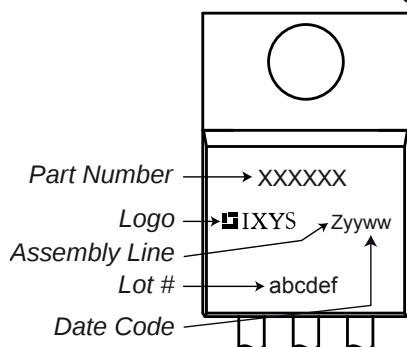


IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{CES}	collector emitter voltage	T _{VJ} = 25°C				1200	V
V _{GES}	max. DC gate voltage					±20	V
V _{GEM}	max. transient gate emitter voltage					±30	V
I _{C25}	collector current	T _C = 25°C				20	A
I _{C100}		T _C = 100°C				13	A
P _{tot}	total power dissipation	T _C = 25°C				85	W
V _{CE(sat)}	collector emitter saturation voltage	I _C = 10A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C		1.8 2.1	2.1	V V
V _{GE(th)}	gate emitter threshold voltage	I _C = 0.3mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	5.4	5.9	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C			0.1	mA mA
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V				500	nA
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 10 A			27		nC
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600V; I _C = 10A V _{GE} = ±15 V; R _G =100 Ω	T _{VJ} = 125°C		70		ns
t _r	current rise time				40		ns
t _{d(off)}	turn-off delay time				250		ns
t _f	current fall time				100		ns
E _{on}	turn-on energy per pulse				1.1		mJ
E _{off}	turn-off energy per pulse				1.1		mJ
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G =100 Ω V _{CEmax} = 1200V	T _{VJ} = 125°C				
I _{CM}						30	A
SCSOA	short circuit safe operating area	V _{CEmax} = 900 V V _{CE} = 900 V; V _{GE} = ±15 V R _G = 100 Ω; non-repetitive	T _{VJ} = 125°C				
t _{SC}	short circuit duration					10	μs
I _{SC}	short circuit current				40		A
R _{thJC}	thermal resistance junction to case					1.5	K/W
R _{thCH}	thermal resistance case to heatsink				0.50		K/W
Diode							
V _{RRM}	max. repetitive reverse voltage	T _{VJ} = 25°C				1200	V
I _{F25}	forward current	T _C = 25°C				22	A
I _{F100}		T _C = 100°C				14	A
V _F	forward voltage	I _F = 10A	T _{VJ} = 25°C T _{VJ} = 125°C			2.20	V V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C			*	mA mA
Q _{rr}	reverse recovery charge	V _R = 600 V -di _F /dt = -250 A/μs I _F = 10A; V _{GE} = 0 V	T _{VJ} = 125°C		1.3		μC
I _{RM}	max. reverse recovery current				10.5		A
t _{rr}	reverse recovery time				350		ns
E _{rec}	reverse recovery energy				0.35		mJ
R _{thJC}	thermal resistance junction to case					1.8	K/W
R _{thCH}	thermal resistance case to heatsink				0.50		K/W

preliminary

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part number

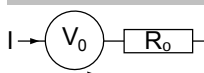
I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 12 = Current Rating [A]
 IF = Copack
 1200 = Reverse Voltage [V]
 PB = TO-220AB (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA12IF1200PB	IXA12IF1200PB	Tube	50	507428

Similar Part	Package	Voltage class
IXA12IF1200HB	TO-247AD (3)	1200
IXA12IF1200TC	TO-268AA (D3Pak) (2)	1200

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150\text{ °C}$  $V_{0\max}$ threshold voltage $R_{0\max}$ slope resistance *

IGBT

1.1

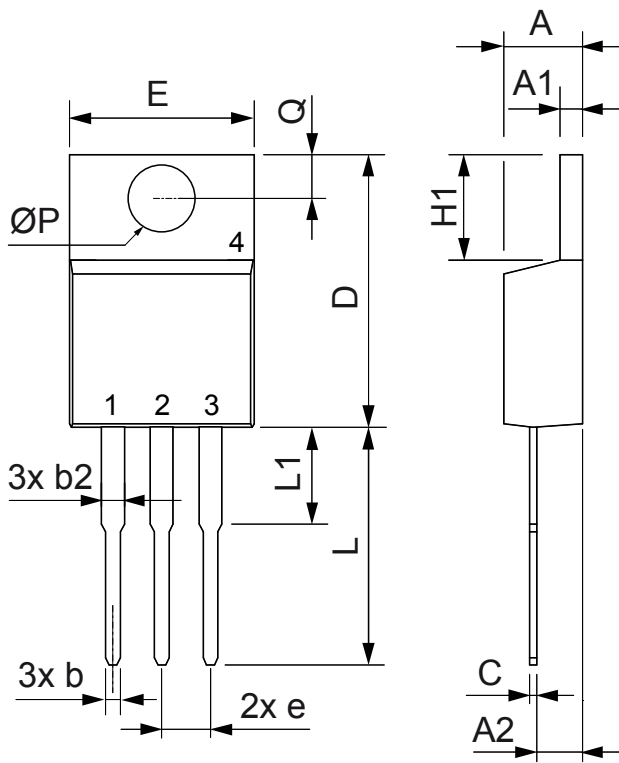
153

Diode

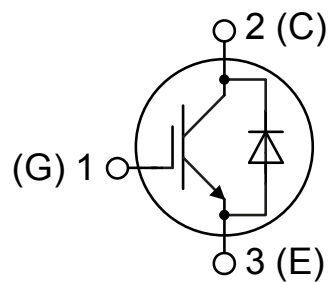
1.25

85 mΩ

V

Outlines TO-220


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



IGBT

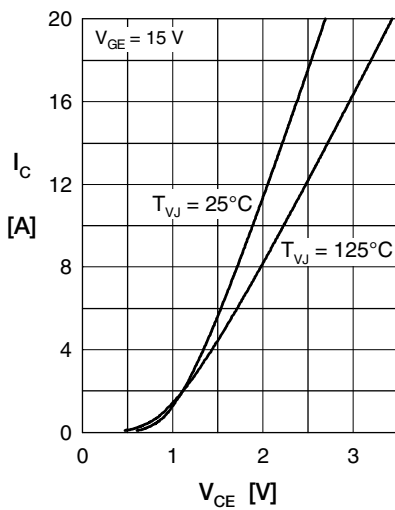


Fig. 1 Typ. output characteristics

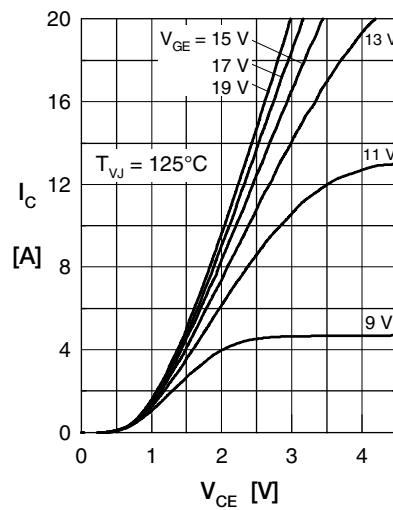


Fig. 2 Typ. output characteristics

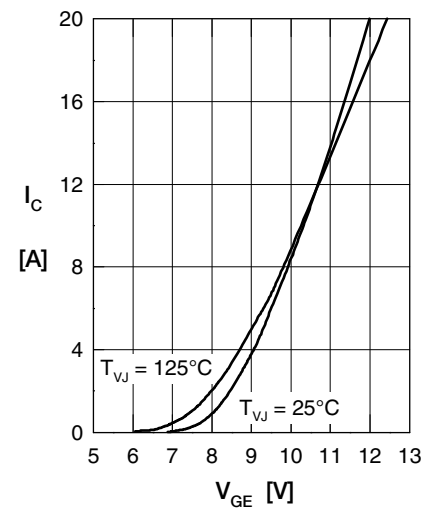


Fig. 3 Typ. transfer characteristics

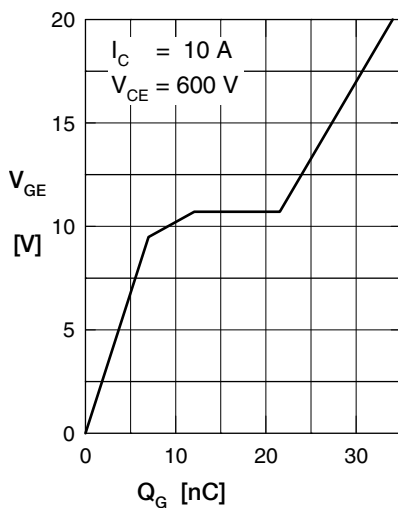


Fig. 4 Typ. turn-on gate charge

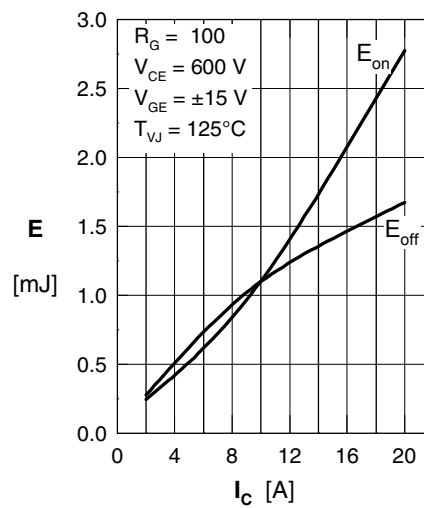


Fig. 5 Typ. switching energy vs. collector current

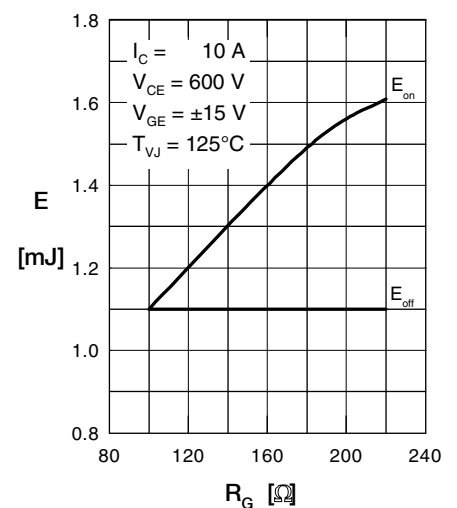


Fig. 6 Typ. switching energy vs. gate resistance

Fig. 7 Typ. transient thermal impedance junction to case

Diode

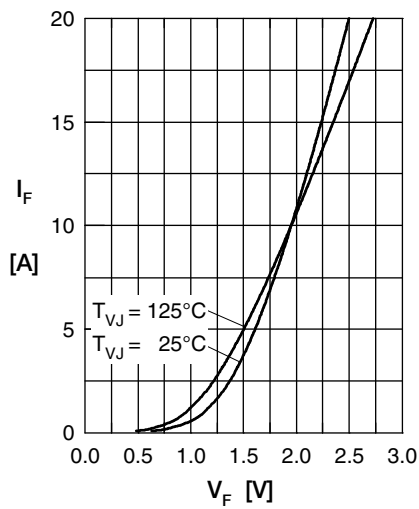


Fig. 1 Typ. forward current versus V_F

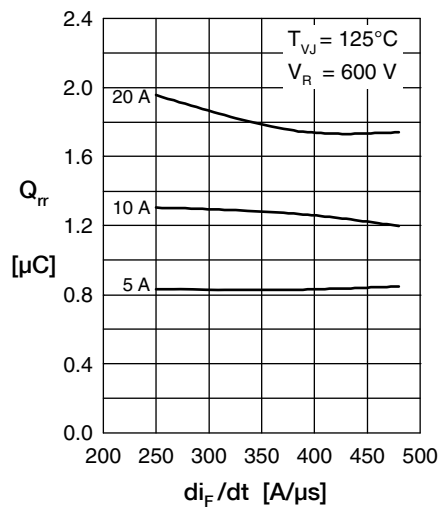


Fig. 2 Typical reverse recov. charge Q_{rr} versus di_F/dt

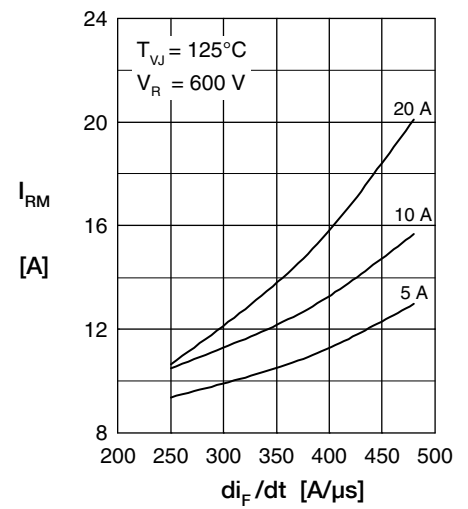


Fig. 3 Typ: peak reverse current I_{RM} versus di_F/dt

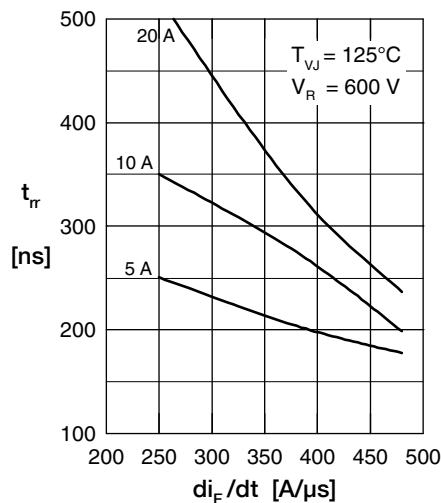


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

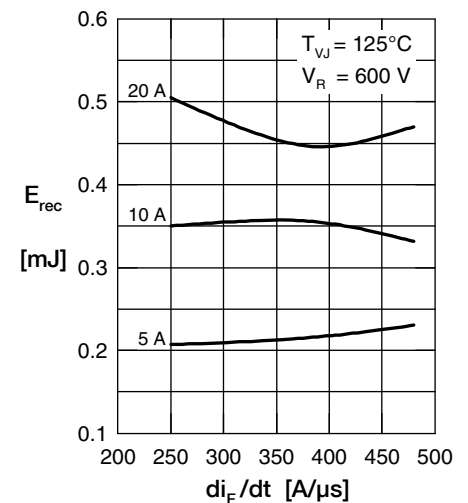


Fig. 6 Typ. recovery energy E_{rec} vs. di_F/dt

Fig. 7 Typ. transient thermal impedance junction to case



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